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# 2SC4264

Silicon NPN Epitaxial

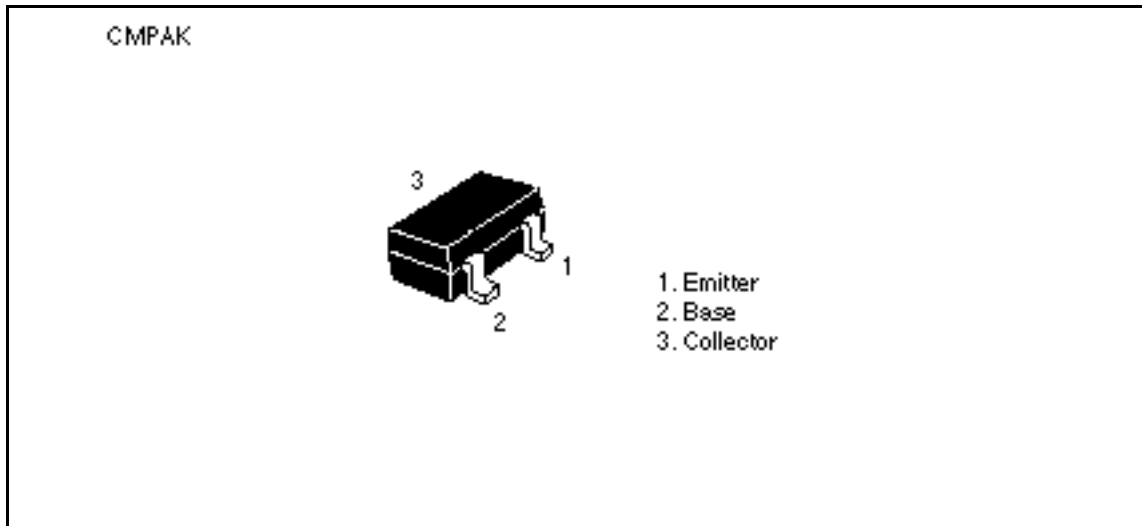
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## Application

VHF / UHF RF amplifier, Local oscillator, Mixer

## Outline



## 2SC4264

### Absolute Maximum Ratings (Ta = 25°C)

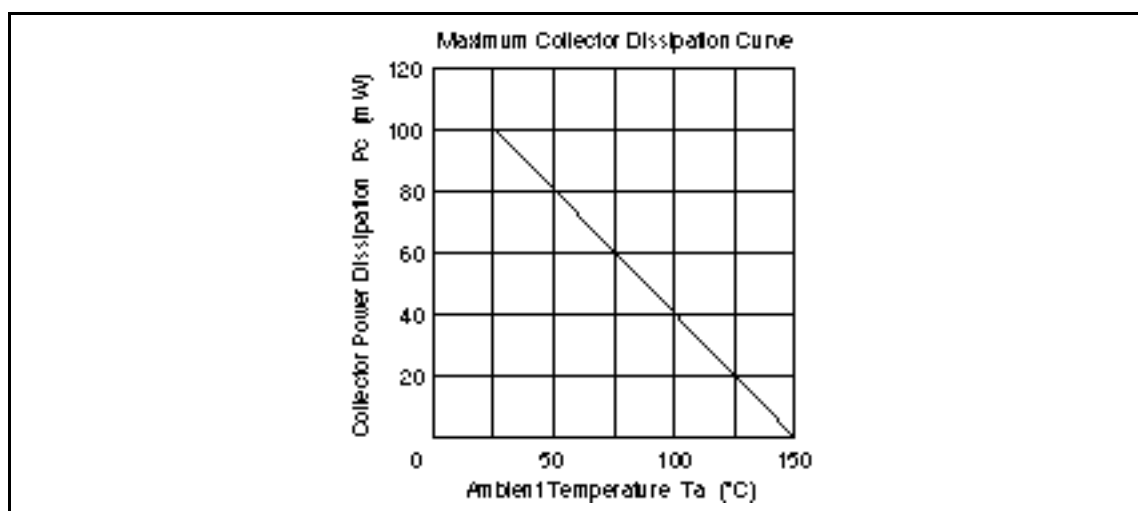
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	20	V
Collector to emitter voltage	$V_{CEO}$	11	V
Emitter to base voltage	$V_{EBO}$	3	V
Collector current	$I_C$	50	mA
Collector power dissipation	$P_C$	100	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector cutoff current	$I_{CBO}$	—	—	0.5	$\mu A$	$V_{CB} = 15 V, I_E = 0$
	$I_{CEO}$	—	—	10	$\mu A$	$V_{CE} = 11 V, R_{BE} =$
Emitter cutoff current	$I_{EBO}$	—	—	1.0	$\mu A$	$V_{EB} = 3 V, I_C = 0$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.7	V	$I_C = 10 mA, I_B = 5 mA$
DC current transfer ratio	$h_{FE}$	20	—	—		$V_{CE} = 10 V, I_C = 5 mA$
Collector output capacitance	$C_{ob}$	—	—	1.5	pF	$V_{CB} = 10 V, I_E = 0, f = 1MHz$
Gain bandwidth product	$f_T$	1.4	—	—	GHz	$V_{CE} = 10 V, I_C = 10 mA$

Note: Marking is "GC".

See characteristic curves of 2SC2734.



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